



2N60L

Power MOSFET

2A, 600V N-CHANNEL POWER MOSFET

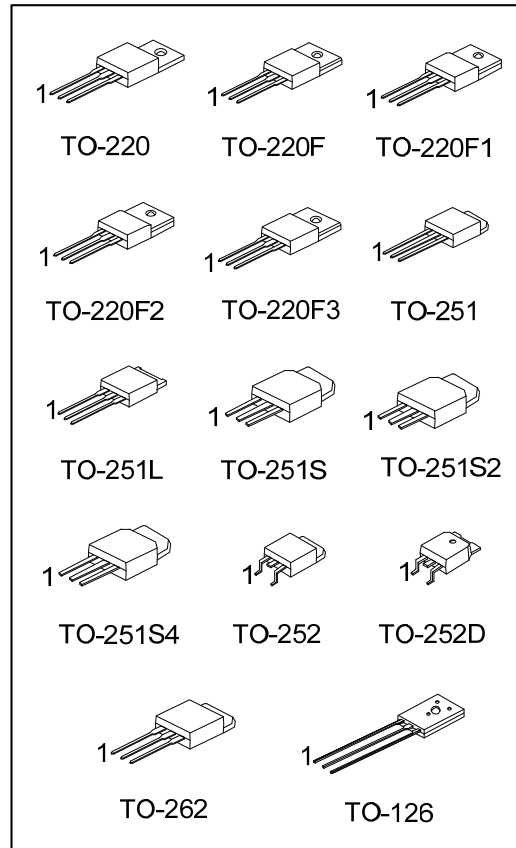
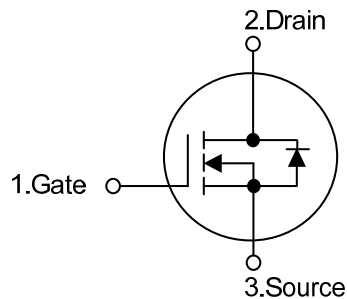
■ DESCRIPTION

The UTC **2N60L** is a high voltage MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

■ FEATURES

- * $R_{DS(ON)} < 5\Omega$ @ $V_{GS} = 10V$, $I_D = 1A$
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

■ SYMBOL



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2N60LL-TA3-T	2N60LG-TA3-T	TO-220	G	D	S	Tube
2N60LL-TF1-T	2N60LG-TF1-T	TO-220F1	G	D	S	Tube
2N60LL-TF2-T	2N60LG-TF2-T	TO-220F2	G	D	S	Tube
2N60LL-TF3-T	2N60LG-TF3-T	TO-220F	G	D	S	Tube
2N60LL-TF3T-T	2N60LG-TF3T-T	TO-220F3	G	D	S	Tube
2N60LL-TM3-T	2N60LG-TM3-T	TO-251	G	D	S	Tube
2N60LL-TMA-T	2N60LG-TMA-T	TO-251L	G	D	S	Tube
2N60LL-TMS-T	2N60LG-TMS-T	TO-251S	G	D	S	Tube
2N60LL-TMS2-T	2N60LG-TMS2-T	TO-251S2	G	D	S	Tube
2N60LL-TMS4-T	2N60LG-TMS4-T	TO-251S4	G	D	S	Tube
2N60LL-TN3-R	2N60LG-TN3-R	TO-252	G	D	S	Tape Reel
2N60LL-TND-R	2N60LG-TND-R	TO-252D	G	D	S	Tape Reel
2N60LL-T2Q-T	2N60LG-T2Q-T	TO-262	G	D	S	Tube
2N60LL-T60-K	2N60LG-T60-K	TO-126	G	D	S	Bulk

Note: Pin Assignment: G: Gate D: Drain S: Source

2N60LL-TA3-T (1) Packing Type (2) Package Type (3) Green Package	(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TF1: TO-220F1, TF2: TO-220F2, TF3: TO-220F, TF3T: TO-220F3, TM3: TO-251, TMA: TO-251L, TMS: TO-251S, TN3: TO-252, TMS2: TO-251S2, TMS4: TO-251S4, TND: TO-252D, T2Q: TO-262, T60: TO-126 (3) L: Lead Free, G: Halogen Free and Lead Free
--	--

MARKING

PACKAGE		MARKING
TO-220 TO-220F TO-220F1 TO-220F2 TO-220F3 TO-251 TO-251L	TO-251S TO-251S2 TO-251S4 TO-252 TO-252D TO-262	UTC 2N60L L: Lead Free G: Halogen Free Lot Code Data Code 1
TO-126		UTC 2N60L Data Code L: Lead Free G: Halogen Free 1

■ **ABSOLUTE MAXIMUM RATINGS** ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V_{GSS}	± 30	V
Avalanche Current (Note 2)		I_{AR}	2.0	A
Drain Current	Continuous	I_D	2.0	A
	Pulsed (Note 2)	I_{DM}	8.0	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	140	mJ
	Repetitive (Note 2)	E_{AR}	4.5	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220/TO-262	P_D	54	W
	TO-220F/TO-220F1 TO-220F3		23	W
	TO-220F2		25	W
	TO-251/TO-251L TO-251S/TO-251S2 TO-251S4/TO-252 TO-252D		44	W
	TO-126		12.5	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Ambient Operating Temperature		T_{OPR}	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by T_J

3. $L=64\text{mH}$, $I_{AS}=2.0\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD}\leq 2.4\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ **THERMAL DATA**

PARAMETER	PACKAGE	SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-220F2 TO-220F3/TO-262	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-251/TO-251L TO-251S/TO-251S2 TO-251S4/TO-252 TO-252D		100	$^\circ\text{C}/\text{W}$
	TO-126		132	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220/TO-262	θ_{JC}	2.32	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1 TO-220F3		5.5	$^\circ\text{C}/\text{W}$
	TO-220F2		5	$^\circ\text{C}/\text{W}$
	TO-251/TO-251L TO-251S/TO-251S2 TO-251S4/TO-252 TO-252D		2.87	$^\circ\text{C}/\text{W}$
	TO-126		10	$^\circ\text{C}/\text{W}$

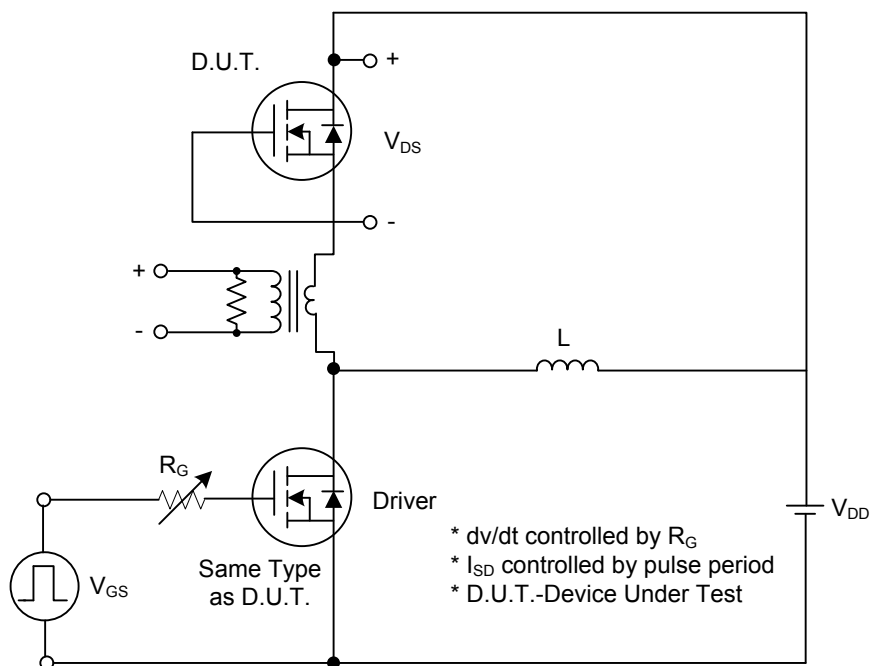
■ **ELECTRICAL CHARACTERISTICS** ($T_J = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} = 0V, I _D = 250μA	600			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} = 600V, V _{GS} = 0V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} = 30V, V _{DS} = 0V			100	nA
	Reverse		V _{GS} = -30V, V _{DS} = 0V			-100	nA
Breakdown Voltage Temperature Coefficient		ΔBV _{DSS} /ΔT _J	I _D =250μA, Referenced to 25°C		0.4		V/°C
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} = 10V, I _D =1A		4.2	5.0	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{ISS}	V _{DS} =25V, V _{GS} =0V, f =1MHz		300	350	pF
Output Capacitance		C _{OSS}			30	50	pF
Reverse Transfer Capacitance		C _{RSS}			7	10	pF
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		t _{D (ON)}	V _{DD} =300V, I _D =2.4A, R _G =25Ω (Note 1, 2)		30	60	ns
Turn-On Rise Time		t _R			25	60	ns
Turn-Off Delay Time		t _{D (OFF)}			70	90	ns
Turn-Off Fall Time		t _F			30	60	ns
Total Gate Charge		Q _G	V _{DS} =480V, V _{GS} =10V, I _D =2.4A (Note 1, 2)		30	40	nC
Gate-Source Charge		Q _{GS}			8		nC
Gate-Drain Charge		Q _{GD}			10		nC
DRAIN-SOURCE DIODE CHARACTERISTICS							
Drain-Source Diode Forward Voltage		V _{SD}	V _{GS} = 0 V, I _{SD} = 2.0 A			1.4	V
Continuous Drain-Source Current		I _{SD}				2.0	A
Pulsed Drain-Source Current		I _{SM}				8.0	A
Reverse Recovery Time		t _{RR}	V _{GS} = 0 V, I _{SD} = 2.4A,		180		ns
Reverse Recovery Charge		Q _{RR}	di/dt = 100 A/μs (Note1)		0.72		μC

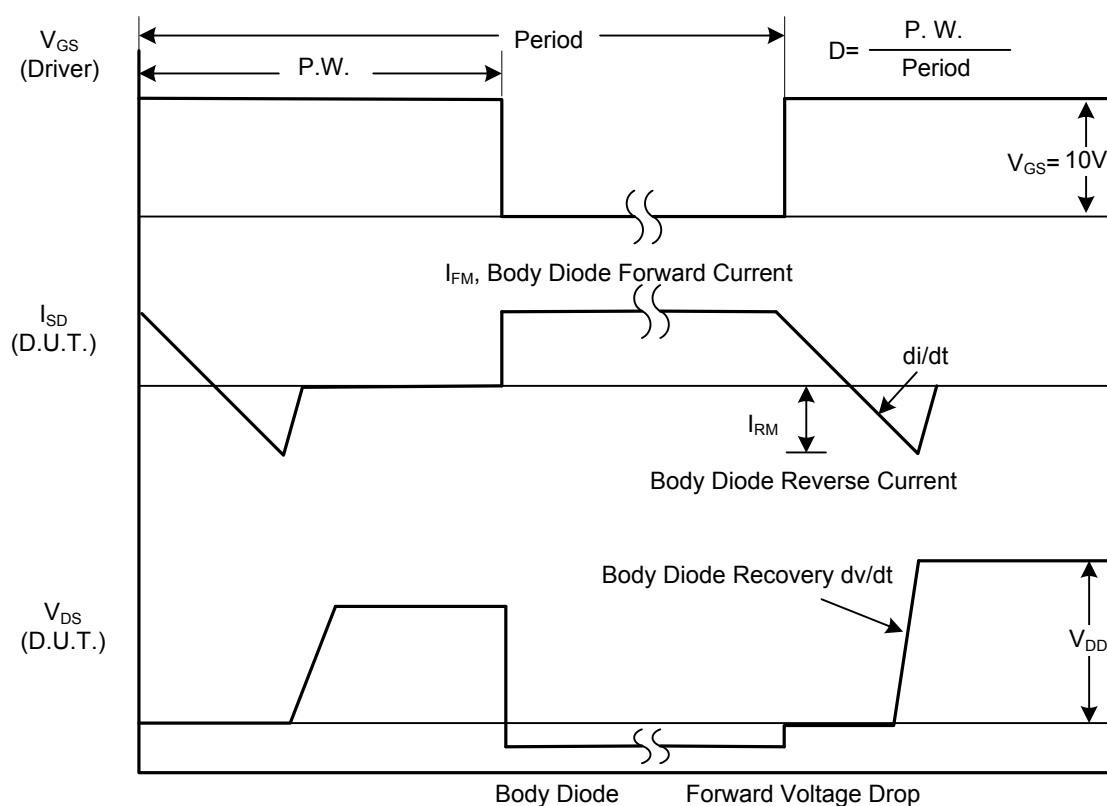
Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

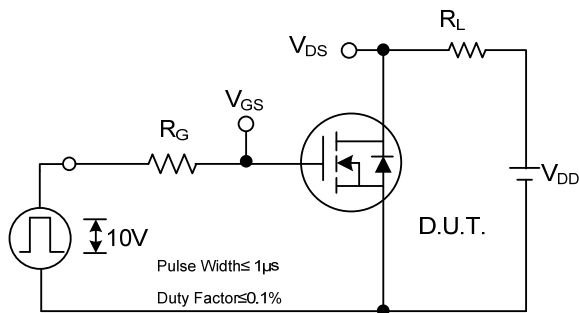


Peak Diode Recovery dv/dt Test Circuit

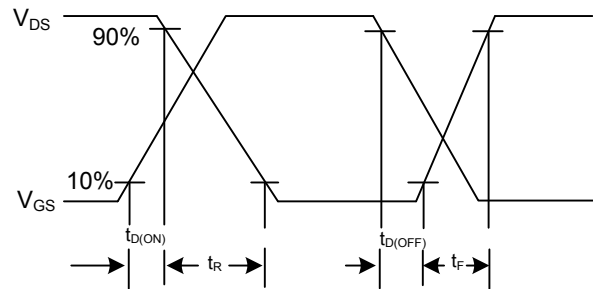


Peak Diode Recovery dv/dt Waveforms

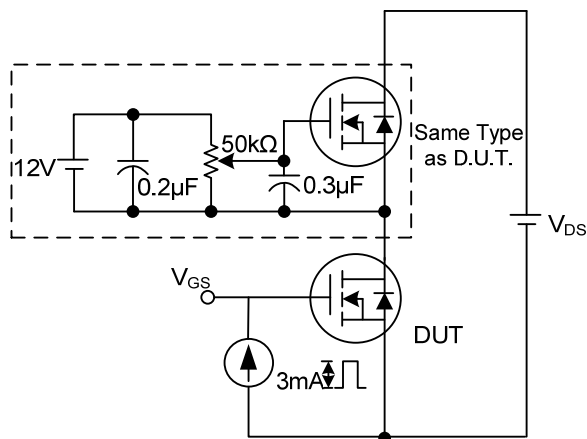
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



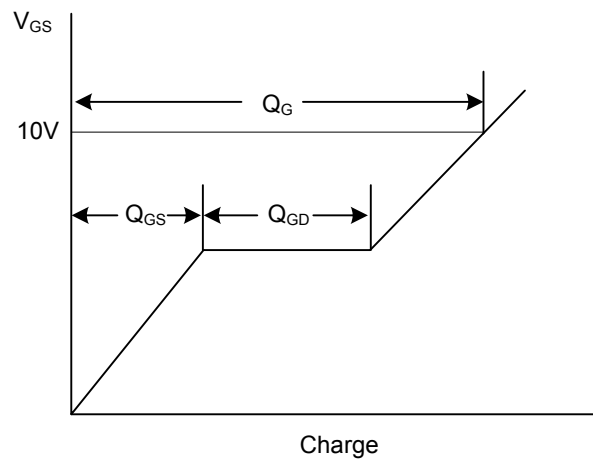
Switching Test Circuit



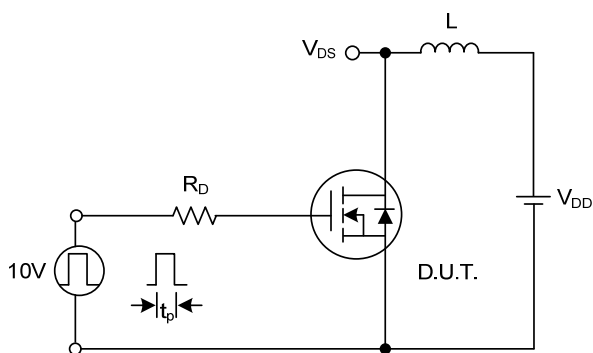
Switching Waveforms



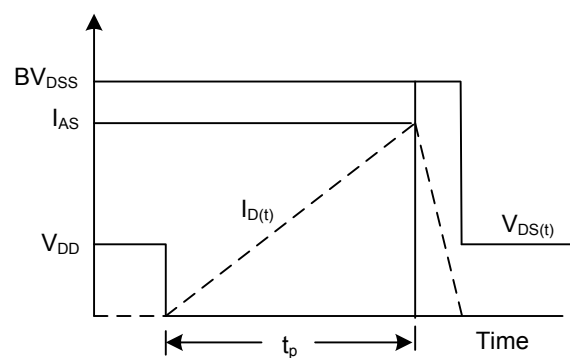
Gate Charge Test Circuit



Gate Charge Waveform

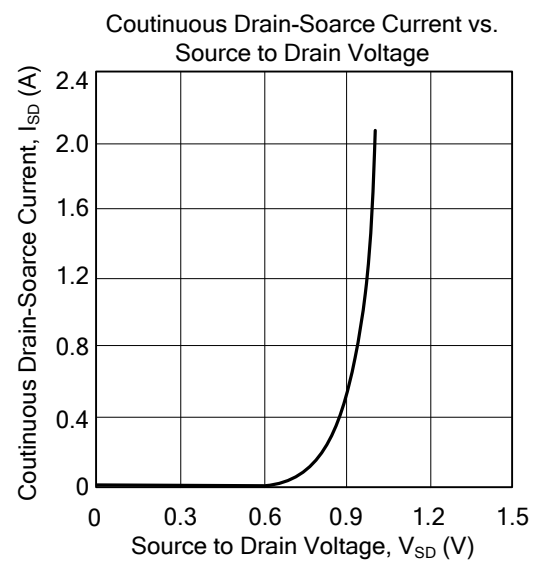
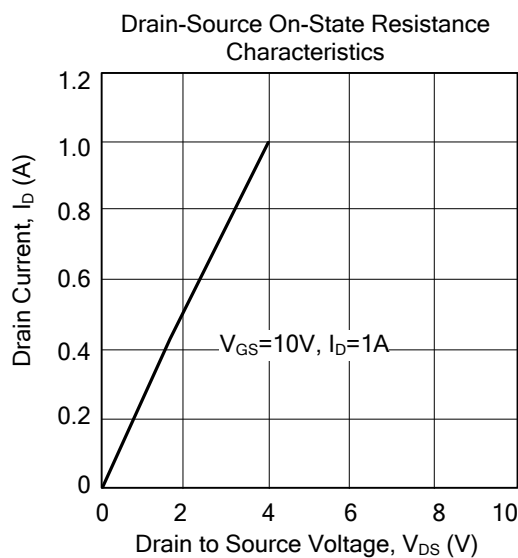
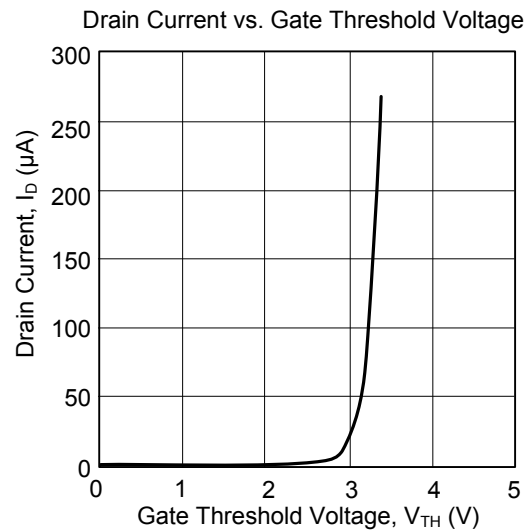
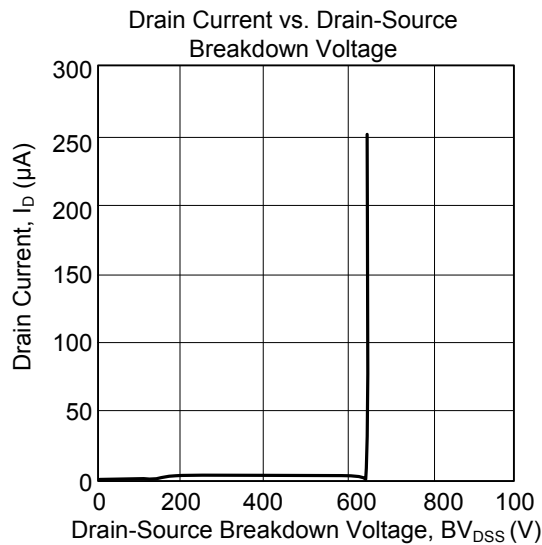


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.